N-channel 80 V, 3 m Ω standard level FET in D2PAK

2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|----------------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | | _ |
| 2 | D | drain ^[1] | mb | |
| 3 | S | source | | |
| mb | D | drain | i3 | |
| | | | | mbb076 S |
| | | | | |
| | | | SOT404 (D2PAK) | |

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

| Type number | Package | | |
|--------------|---------|--|---------|
| | Name | Description | Version |
| PSMN2R8-80BS | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

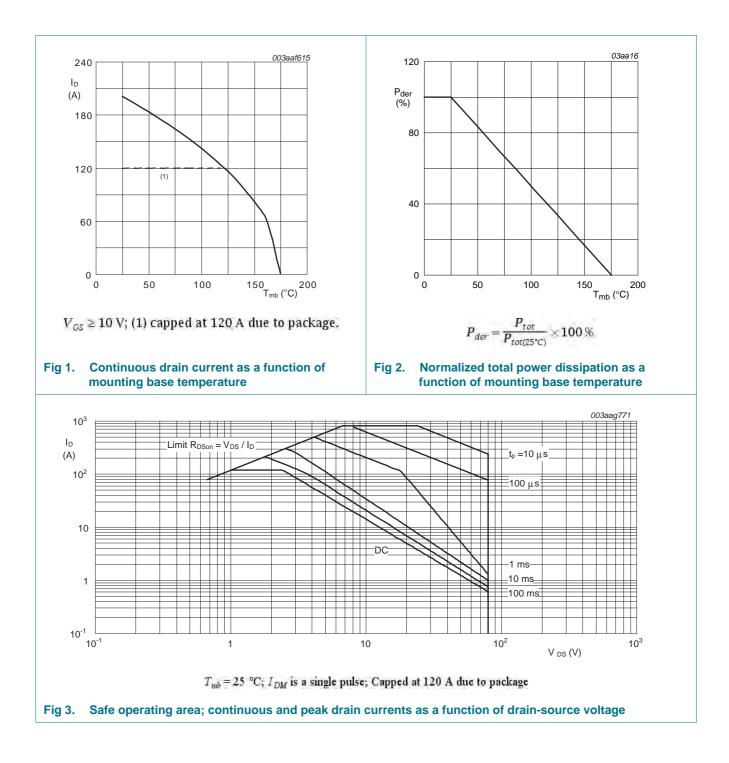
| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------------|---|--|--------------|-----|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 80 | V |
| V _{DGR} | drain-gate voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | 80 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u> | <u>[1]</u> - | 120 | А |
| | | V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u> | <u>[1]</u> - | 120 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3 | - | 824 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | 306 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | - | 260 | °C |
| Source-drain | n diode | | | | |
| I _S | source current | T _{mb} = 25 °C | <u>[1]</u> - | 120 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 824 | А |
| Avalanche r | uggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; unclamped | - | 676 | mJ |

[1] Continuous current is limited by package.

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|--------------------|--|---|
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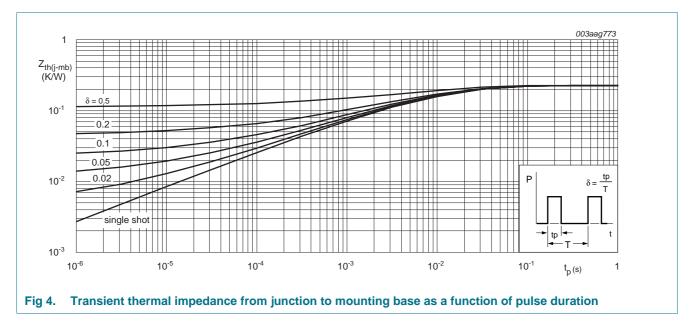
N-channel 80 V, 3 m Ω standard level FET in D2PAK



N-channel 80 V, 3 m Ω standard level FET in D2PAK

5. Thermal characteristics

| Table 5. | Thermal characteristics | | | | | |
|-----------------------|---|---|-----|------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-mb)} | thermal resistance from junction to mounting base | see <u>Figure 4</u> | - | 0.22 | 0.49 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint; mounted on a printed-circuit board | - | 50 | - | K/W |



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N-channel 80 V, 3 mΩ standard level FET in D2PAK

Characteristics 6.

| Table 6. | Characteristics | | | | | |
|------------------------|--------------------------------------|---|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _{(BR)DSS} | drain-source | I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C | 73 | - | - | V |
| | breakdown voltage | $I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$ | 80 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u> | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10 | - | - | 4.6 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u> | 2 | 3 | 4 | V |
| I _{DSS} | drain leakage current | V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C | - | 0.02 | 10 | μA |
| | | V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | 10 | 100 | nA |
| | | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 10 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u> | - | 6.12 | 7.2 | mΩ |
| | | V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12; see Figure 13 | - | 4.21 | 5 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u> | - | 2.55 | 3 | mΩ |
| R _G | internal gate resistance (AC) | f = 1 MHz | - | 0.9 | - | Ω |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$ | - | 135 | - | nC |
| | | $I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 139 | - | nC |
| Q _{GS} | gate-source charge | see Figure 14; see Figure 15 | - | 51 | - | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | - | 30 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate-source charge | | - | 21 | - | nC |
| Q _{GD} | gate-drain charge | | - | 27 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | $I_D = 75 \text{ A}; V_{DS} = 40 \text{ V}; \text{see } \frac{\text{Figure } 14}{\text{Figure } 15}$ | - | 5.8 | - | V |
| C _{iss} | input capacitance | V _{DS} = 40 V; V _{GS} = 0 V; f = 1 MHz; | - | 9961 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; see <u>Figure 16</u> | - | 847 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 401 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.53 \Omega; \text{ V}_{GS} = 5 \text{ V};$ | - | 41 | - | ns |
| t _r | rise time | $R_{G(ext)} = 10 \ \Omega; \ I_D = 75 \ A$ | - | 43 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 109 | - | ns |
| t _f | fall time | | - | 44 | - | ns |

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Symbol

Source-drain diode

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Тур

Max

Unit

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Min

| | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V};$ see <u>Figure 17</u> | T _j = 25 °C; | - | 0.8 | 1.2 | V |
|---|-----------------------------------|---|--------------------------------------|------------------------------|---------------------------------|-------------------|----|
| r | reverse recovery time | $I_{\rm S} = 25 \text{ A}; \text{ d}I_{\rm S}/\text{d}t = 10$ | 0 A/µs; V _{GS} = 0 V; | - | 63 | - | ns |
|) _r | recovered charge | V _{DS} = 20 V | | - | 121 | - | nC |
| 250 g _{fs} (S) 200 | | 003aaf602 | 75 I _D (A) | | | 003aaf603 | |
| 150 | | | 50 | | | | |
| 50 | | | 25 | T _j = 175 °C | | = 25 ∘C | |
| 0 0 | 20 40 | 60 80 I _D (A) | 0 0 | 2 | / 4 _{V_G} | 6 | |
| | $T_j = 25 ^{\circ}C; V_{DS} = 25$ | | | $V_{DS} > I_D \times R$ | | | |
| | ward transconductance a | | | | | | |
| drai | in current; typical values | as a function of | Fig 6. Transfer cha function of g | aracteristics gate-source | | | |
| drai 16000 C (pF) 12000 | | | | | voltage | | |
| 16000 C (pF) | | 003aaf606 | function of g | gate-source | voltage | ; typical | |
| 16000 C (pF) 12000 | | 003aaf606 C _{iss} | function of g | gate-source | Voltage | 2003aad685 4.5 | |
| 16000 C (pF) 12000 8000 4000 | in current; typical values | 003aaf606 | function of g | gate-source | Voltage | () = 4 | |

Table 6. Characteristics ...continued

Parameter

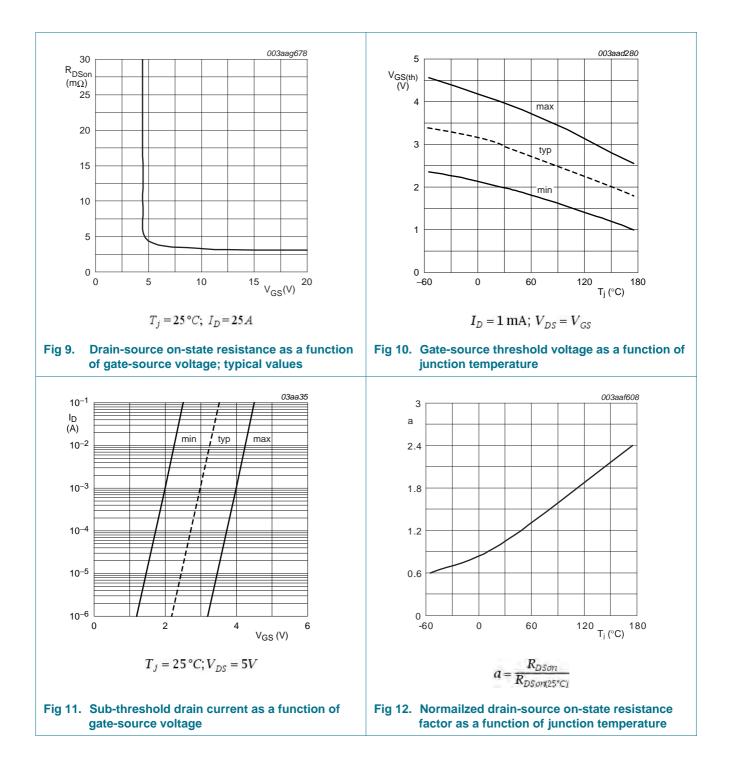
Conditions

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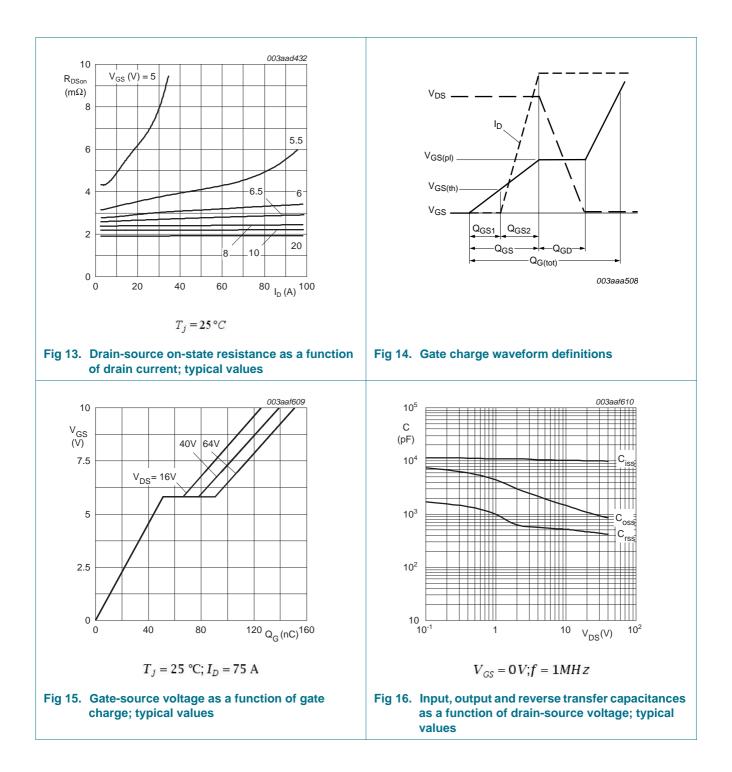


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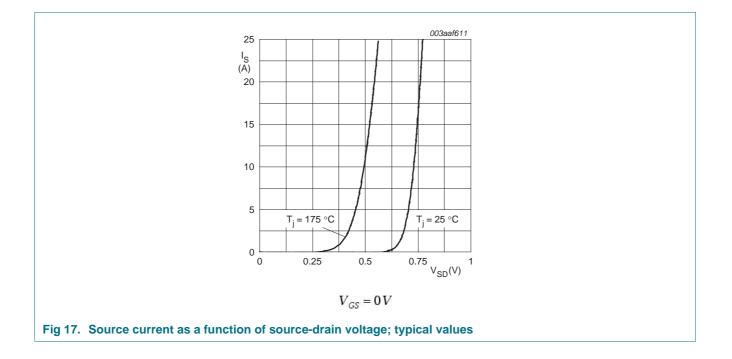


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7. Package outline

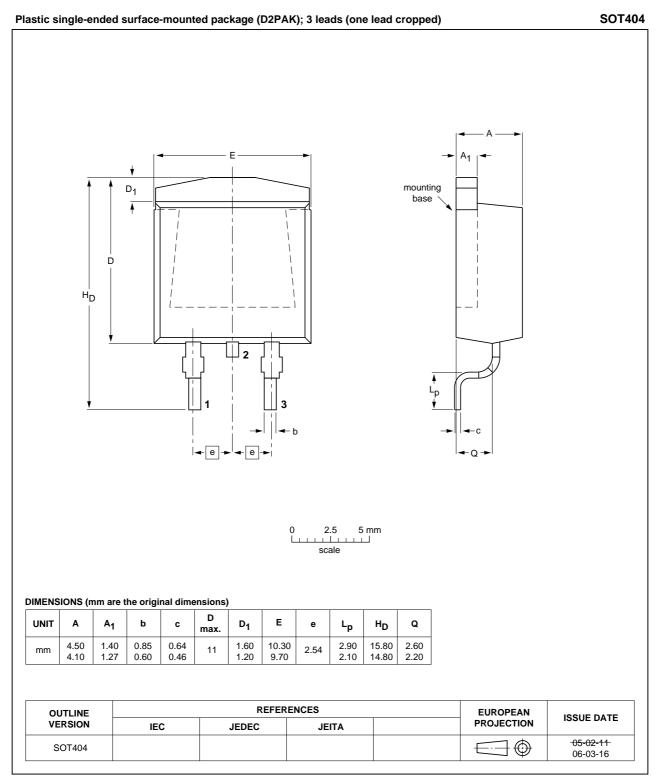


Fig 18. Package outline SOT404 (D2PAK)

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8. Revision history

| Table 7.Revision h | nistory | | | |
|--------------------|-----------------------------------|------------------------------|---------------|------------------|
| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| PSMN2R8-80BS v.2 | 20120229 | Product data sheet | - | PSMN2R8-80BS v.1 |
| Modifications: | Status change | d from objective to product. | | |
| | Various chang | es to content. | | |
| PSMN2R8-80BS v.1 | 20110928 | Objective data sheet | - | - |

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|--------------------------------|-------------------------------|---|
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[2] The term 'short data sheet' is explained in section "Definitions".

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